Si3865CDV vs. Si3865BDV

Description: **Load Switch with Level-Shift**
Package: **TSOP-6**
Pin Out: **Identical**

Part Number Replacements: Si3865CDV-T1-E3 replaces Si3865BDV-T1-E3

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
PARAMETER		**SYMBOL**	**Si3865CDV**	**Si3865BDV**	**UNIT**
Input Voltage		V_{IN}	12	8	V
On/Off Voltage		$V_{ON/OFF}$	8	8	
Load Current	Continuous	I_L	± 2.8	± 2.9	A
	Pulsed		± 6	± 6	
Continuous Intrinsic Diode Conduction		I_S	- 1	- 1	
Power Dissipation		P_D	0.83	0.83	W
Operating Junction and Storage Temperature Range		T_J and T_{stg}	- 55 to 150	- 55 to 150	°C
Maximum Junction-to-Ambient		R_{thJA}	150	150	°C/W

SPECIFICATIONS T_J = 25 °C, unless otherwise noted									
			Si3865CDV			**Si3865BDV**			
PARAMETER		**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Off Characteristic									
Reverse Leakage Current		I_{FL}			1			1	µA
Diode Forward Voltage		V_{SD}		- 0.75	- 1		- 0.77	- 1	V
Dynamic									
Input Voltage Range		V_{IN}	1.8		12	1.8		8	V
On-Resistance (P-Channel) at 1 A	V_{IN} = 4.5 V	$R_{DS(on)}$		0.050	0.060		0.045	0.060	W
	V_{IN} = 2.5 V			0.073	0.095		0.075	0.100	
	V_{IN} = 1.8 V			0.100	0.130		0.135	0.175	
On-State (P-Channel) Drain-Current	V_{IN} = 5 V	$I_{D(on)}$	1			1			A
	V_{IN} = 3 V		1			1			

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.